

## R-C Thermal Model Parameters

### DESCRIPTION

The parametric values in the R-C thermal model have been derived using curve-fitting techniques. These techniques are described in "[A Simple Method of Generating Thermal Models for a Power MOSFET](#)"[1]. When implemented in P-Spice, these values have matching characteristic curves to the Single Pulse Transient Thermal Impedance curves for the MOSFET.

R-C values for the electrical circuit in the Foster/Tank and Cauer/Filter configurations are included.

*Note:*

*For a detailed explanation of implementing these values in P-SPICE, refer to [Application Note AN609 Thermal Simulations Of Power MOSFETs on P-SPICE Platform](#).*

### R-C THERMAL MODEL FOR TANK CONFIGURATION



<b>R-C VALUES FOR TANK CONFIGURATION</b>			
Thermal Resistance (°C/W)			
Junction to	Ambient	Case	Foot
RT1	6.8093	N/A	22.8576
RT2	34.9647	N/A	6.8294
RT3	26.3902	N/A	6.2761
RT4	56.8358	N/A	9.0369
Thermal Capacitance (Joules/°C)			
Junction to	Ambient	Case	Foot
CT1	162.8778 u	N/A	1.4095 m
CT2	2.0906 m	N/A	171.5347 u
CT3	40.2409 m	N/A	262.5130 m
CT4	1.3951	N/A	11.4353 m

*This document is intended as a SPICE modeling guideline and does not constitute a commercial product data sheet. Designers should refer to the appropriate data sheet of the same number for guaranteed specification limits.*

**R-C THERMAL MODEL FOR FILTER CONFIGURATION****R-C VALUES FOR FILTER CONFIGURATION**

Thermal Resistance ( $^{\circ}\text{C}/\text{W}$ )			
Junction to	Ambient	Case	Foot
RF1	9.3063	N/A	5.3345
RF2	39.1718	N/A	5.7488
RF3	22.7273	N/A	26.8876
RF4	53.7946	N/A	7.0291
Thermal Capacitance (Joules/ $^{\circ}\text{C}$ )			
Junction to	Ambient	Case	Foot
CF1	180.1369 u	N/A	110.7145 u
CF2	2.1877 m	N/A	352.3051 u
CF3	60.8164 m	N/A	1.0915 m
CF4	1.4512	N/A	168.0905 m

Note: NA indicates not applicable

Reference:

[1] "A Simple Method of Generating Thermal Models for a Power MOSFET" by Wharton McDaniel and Kandarp Pandya, IEEE / SEMITHERM 2002

